V-Cell

Halfcut Series

TSSCN

Mono c-Si Solar Cell (Bi-Facial/Ares)





-High

Physical Characteristics

Dimensions Diagonal	182mm X 182mm ± 0.5mm 247mm± 0.5mm					
Thickness(Si)	170 μ m \pm 50 μ m					
Front(-)	Alkaline texturized surface with silicon nitride anti-reflecting coating					
	10 X 0.12mm ± 0.1mm bus bars					
	Distance between bus bars : 18mm					
Back(+)	Local aluminum back surface field					

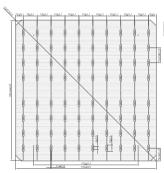
Distance between bus bars: 18mm



- -High Cell-To- Module ratio through precise cell conversion efficiency sorting, classified efficiency grade by both minimum power and current.
- -Excellent electrical long-term stability and reliability by using of best raw materials and through strict quality inspection control.
- -Low breakage rate by using high qualified and stable wafers.
- -High quality homogeneous appearance by sorting into defined color classes.
- -100% screened for reverse current and shunt resistance.
- -Excellent passivation quality of the rear side compared to the traditional solar cell is clearly visible in the long wavelength regime.
- -The best solution for PV module with above 440W(6x20) and 530W(6x24) outputs.

Quality Control and Professional Service

- -Regular calibration of test equipment using Fraunhofer ISE reference cell.
- -Environmental friendly due to REACH-SVHC and RoHS compliances.
- -Professional on-site service and support for module certification.
- -Regular light source AAA class calibration for stable conversion efficiency.
- -Lowest LID by periodic monitoring and superior wafer incoming control.



10 X 8 soldering pads, 1.3mm±0.3mm wide bus bars

Electrical Characteristics

	L tecti icat	ectificat Offar acter istics													
	Efficiency Code		234	233	232	231	230	229	228	227	226	225	224	223	222
í	Efficiency	Eff[%]	23.40	23.30	23.20	23.10	23.00	22.90	22.80	22.70	22.60	22.50	22.40	22.30	22.20
Į	Power	Pmpp(W)	7.73	7.69	7.66	7.63	7.59	7.56	7.53	7.49	7.46	7.43	7.40	7.36	7.33
	Max. Power Current	Impp(A)	13.191	13.145	13.116	13.075	13.055	13.037	13.024	13.012	13.001	12.989	12.976	12.955	12.928
	Short Circuit Current	Isc(A)	13.902	13.841	13.825	13.810	13.796	13.781	13.768	13.755	13.743	13.729	13.715	13.687	13.653
	Max. Power Voltage	Vmpp(V)	0.586	0.585	0.584	0.583	0.582	0.580	0.578	0.576	0.574	0.572	0.570	0.568	0.567
	Open Circuit Voltage	Voc(V)	0.692	0.692	0.691	0.689	0.688	0.687	0.686	0.684	0.683	0.681	0.679	0.677	0.675

Standard test condition: AM1.5, 1000W/m², 25°c Average accuracy of all tests is +/-1.5% rel.

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Temperature Coefficients

Current Temperature Coefficient	a(ISC)	0.0423%/K
Voltage Temperature Coefficient	β(VOC)	-0.2903%/K
Power Temperature Coefficient	γ(Pmax)	-0.3535%/K

Standard test condition: AM1.5, 1000W/m2, 25°c

Processing Recommendations

Solder Joint

Copper ribbons coated with $15\sim25\mu m$: 62%Sn/36%Pb/2%Aq or 60%Sn/40%Pb

Standard test condition: AM1.5, 1000W/m2, 25°c

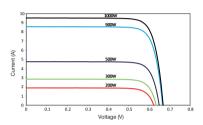
Solderability

Peel Strength Minimum

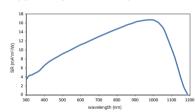
>1.25 N/mm

Soldering results may differ due to different flux, ribbons, soldering methods, and parameters.

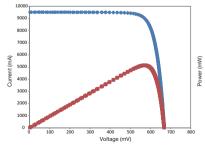
Typical Current-Voltage Curve



Typical Spectral Response

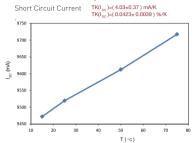


Typical IV-Power Curve

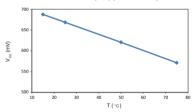


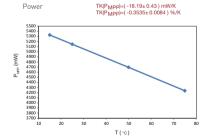
- * All data measured under standard testing condition (STC): 1000 W/m², AM 1.5, 25 °C.
- * All figures bear ±2% tolerance.
- * Reference cell are under testing by Fraunhofer ISE in Freiburg.

Calculated Temperature Coefficients









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Specifications are subject to change without prior notice.
TSEC reserves the rights of final interpretation
and revision of datasheet.